**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic level compatible
- · Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

## 3. Applications

- Relay driver
- · High-speed line driver
- · High-side loadswitch
- · Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-70	V	
$V_{GS}$	gate-source voltage			-20	-	20	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-2.4	Α	
Static characte	Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -10 V; $I_D$ = -2.4 A; $T_j$ = 25 °C		-	130	167	mΩ	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	4	D
2	D	drain		
3	S	source		G $\downarrow$ $\downarrow$ $\downarrow$
4	D	drain	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	S 017aaa259

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PMT200EPEA	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking code
PMT200EPEA	T2EPEA

## 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-70	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C	[1]	-	-2.4	Α
		V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 100 °C	[1]	-	-1.5	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-9.7	Α
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; $I_D$ = -1.3 A; DUT in avalanche (unclamped)		-	19.5	mJ
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	800	mW
			[1]	-	1.75	W
		T <sub>sp</sub> = 25 °C		-	8.3	W
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	diode					
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.8	Α
ESD maximun	n rating		'	'	<u> </u>	
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. Measured between all pins.

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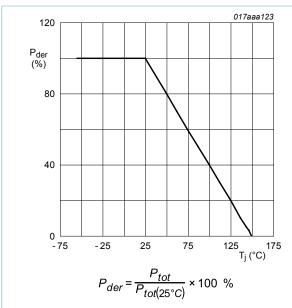


Fig. 1. Normalized total power dissipation as a function of junction temperature

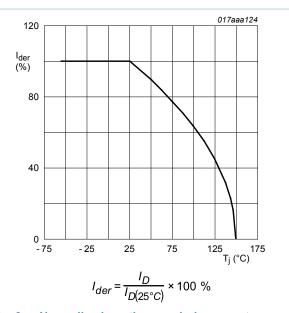


Fig. 2. Normalized continuous drain current as a function of junction temperature

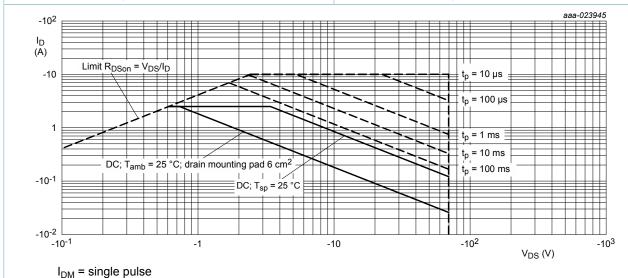


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	III II ee ali	[1]	-	135	155	K/W
	from junction to ambient		[2]	-	54	70	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	7	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

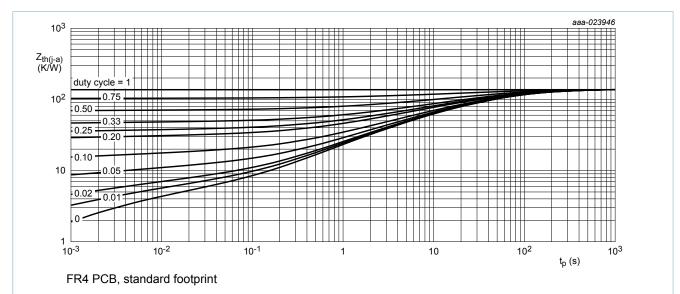
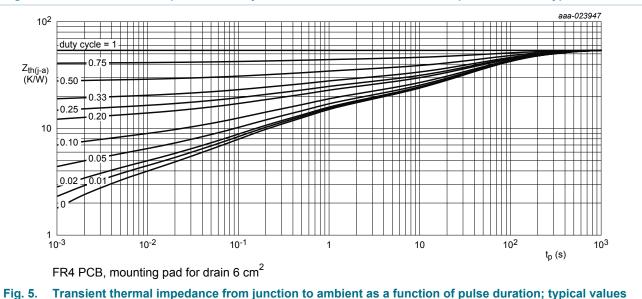


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



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### 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			,
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C}$	-70	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-1	-2	-3	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -70 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	2	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-2	μA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -10 V; $I_D$ = -2.4 A; $T_j$ = 25 °C	-	130	167	mΩ
	resistance	V <sub>GS</sub> = -10 V; I <sub>D</sub> = -2.4 A; T <sub>j</sub> = 150 °C	-	234	250	mΩ
		$V_{GS} = -4.5 \text{ V}; I_D = -2.1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	150	225	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_D$ = -2.4 A; $T_j$ = 25 °C	-	13.5	-	S
$R_G$	gate resistance	f = 1 MHz	-	12	-	Ω
Dynamic ch	naracteristics		,			_
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -35 \text{ V}; I_D = -2.4 \text{ A}; V_{GS} = -10 \text{ V};$	-	10.6	15.9	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	2.2	-	nC
Q <sub>GD</sub>	gate-drain charge		-	1.05	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -35 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	822	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	47	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	31.5	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -35 V; $I_{D}$ = -2.4 A; $V_{GS}$ = -10 V;	-	6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	8	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	42	-	ns
t <sub>f</sub>	fall time		-	20	-	ns
Source-dra	in diode		1			,
V <sub>SD</sub>	source-drain voltage	$I_S = -2.4 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.8	-1.2	V
		1				

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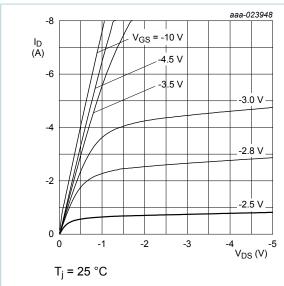


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

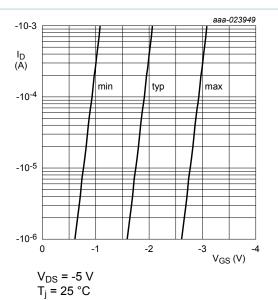


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

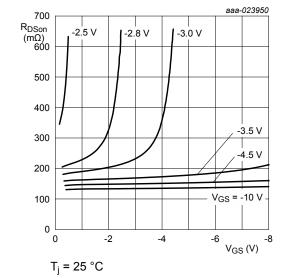


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

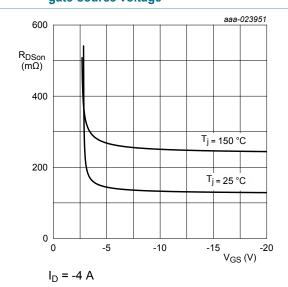


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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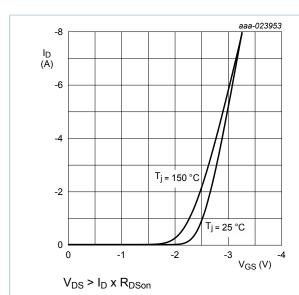


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

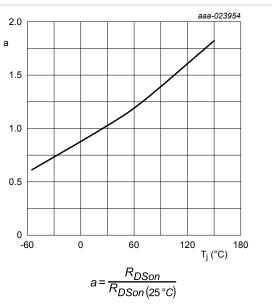


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

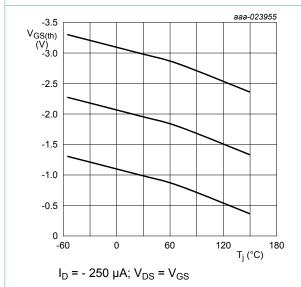


Fig. 12. Gate-source threshold voltage as a function of junction temperature

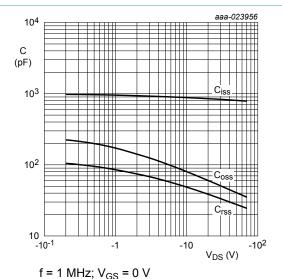
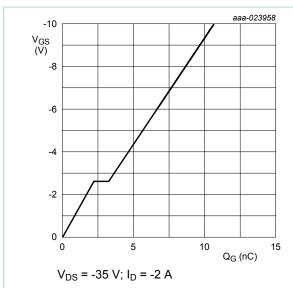


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V<sub>GS</sub>(pl)
V<sub>GS</sub>(th)
V<sub>GS</sub>
Q<sub>GS1</sub>
Q<sub>GS2</sub>
Q<sub>GG</sub>(tot)
003aaa508

Fig. 15. Gate charge waveform definitions

Fig. 14. Gate-source voltage as a function of gate charge; typical values

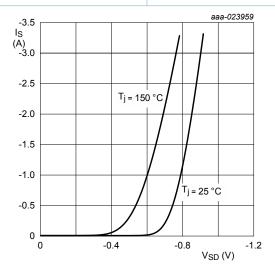
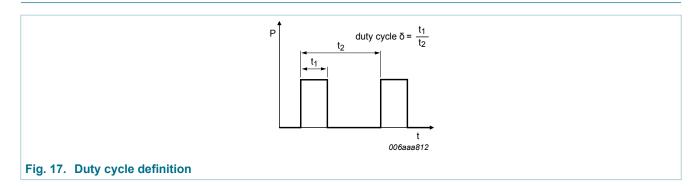


Fig. 16. Source current as a function of source-drain voltage; typical values

### 11. Test information

 $V_{GS} = 0 V$ 



PMT200EPEA

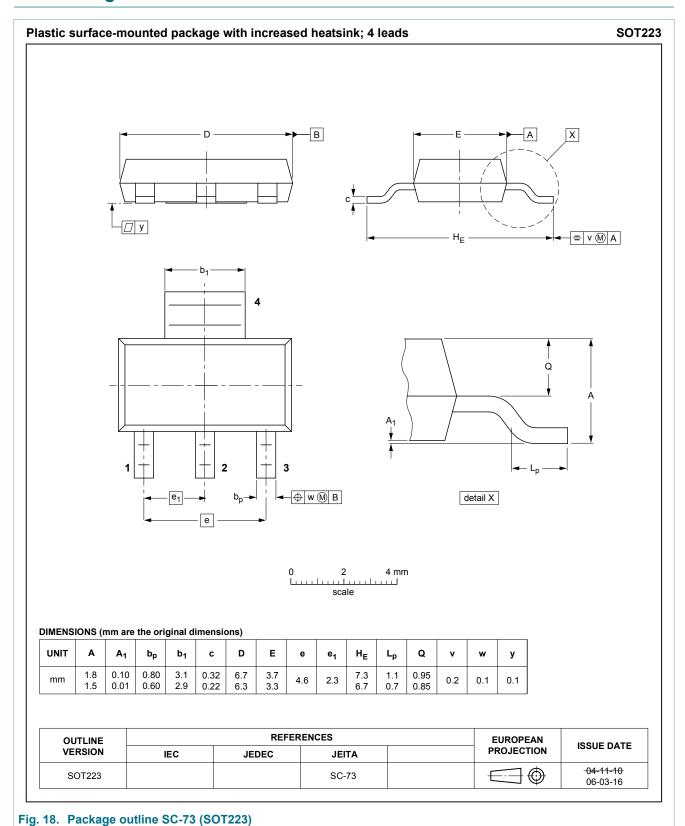
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### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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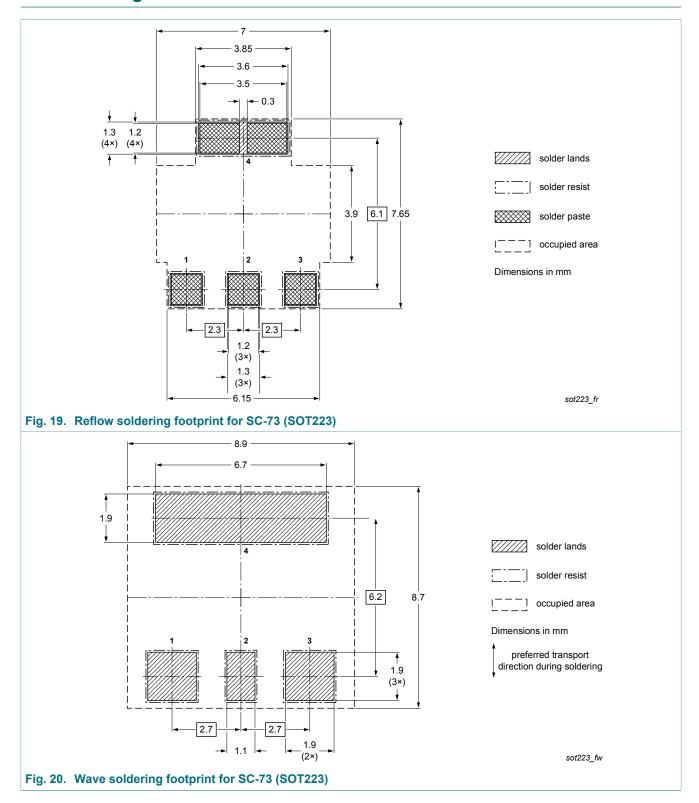
# 12. Package outline



1 lg. 10. 1 ackage outilite 00-73 (001225)

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## 13. Soldering



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# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMT200EPEA v.2	20161026	Product data sheet	-	20160707			
Modification:	<ul> <li>Product status changed</li> <li>Value of I<sub>S</sub> = source current corrected (section 8 Limiting values)</li> </ul>						
PMT200EPEA v.1	20160707	Preliminary data sheet	-	-			

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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